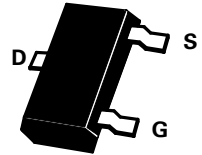


ZVP3310F

FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)}=20\Omega$

COMPLEMENTARY TYPE - ZVN3310F



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	-100	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	75	mA
Pulsed Drain Current	I_{DM}	-1.2	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	-100		V	$I_D=-1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	-1.5	-3.5	V	$I_D=-1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		-20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	I_{DSS}		-1 -50	μA μA	$V_{DS}=-100V, V_{GS}=0$ $V_{DS}=-80V, V_{GS}=0V, T=125^{\circ}C$
On-State Drain Current	$I_{D(on)}$	-300		mA	$V_{DS}=-25V, V_{GS}$
Static Drain-Source On-State Resistance	$R_{DS(on)}$		20	Ω	$V_{GS}=-10V, I_D=-150mA$
Forward Transconductance	g_{fs}	50		mS	$V_{DS}=-25V, I_D=-150mA$
Input Capacitance	C_{iss}		50	pF	$V_{DS}=-25V, V_{GS}=0V, f=1MHz$
Common Source Output Capacitance	C_{oss}		15	pF	
Reverse Transfer Capacitance	C_{rss}		5	pF	
Turn-On Delay Time	$t_{d(on)}$		8	ns	$V_{DD}=-25V, I_D=-150mA$
Rise Time	t_r		8	ns	
Turn-Off Delay Time	$t_{d(off)}$		8	ns	
Fall Time	t_f		8	ns	